



**YEA SHIN TECHNOLOGY CO., LTD**

**YS3907ZBB**

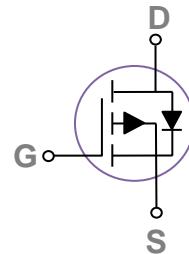
**P-Channel Enhancement MOSFET**  
**VDS= -30V, ID= -30A**



**Features**

- $-30V, -30A, RDS(ON) = 18m\Omega @ VGS = -10V$
- *Fast switching*
- *Green Device Available*
- *Suit for -4.5V Gate Drive Applications*

**PPAK3x3 Pin Configuration**



**Applications**

- *MB / VGA / Vcore*
- *POL Applications*
- *Load Switch*
- *LED Application*

**Absolute Maximum Ratings  $T_c=25^\circ C$  unless otherwise noted**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $T_c=25^\circ C$ )	-30	A
	Drain Current – Continuous ( $T_c=100^\circ C$ )	-19	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	-120	A
$P_D$	Power Dissipation ( $T_c=25^\circ C$ )	27	W
	Power Dissipation – Derate above $25^\circ C$	0.22	W/ $^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

**Thermal Characteristics**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	4.6	$^\circ C/W$

# DEVICE CHARACTERISTICS

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Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)

### Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=-250\mu\text{A}$	-30	---	---	V
$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	$\text{BV}_{\text{DSS}}$ Temperature Coefficient	Reference to $25^\circ\text{C}$ , $\text{I}_D=-1\text{mA}$	---	-0.03	---	$^\circ\text{C}$
$\text{I}_{\text{DSS}}$	Drain-Source Leakage Current	$\text{V}_{\text{DS}}=-27\text{V}, \text{V}_{\text{GS}}=0\text{V}, T_J=25^\circ\text{C}$	---	---	-1	$\mu\text{A}$
		$\text{V}_{\text{DS}}=-24\text{V}, \text{V}_{\text{GS}}=0\text{V}, T_J=125^\circ\text{C}$	---	---	-10	$\mu\text{A}$
$\text{I}_{\text{GSS}}$	Gate-Source Leakage Current	$\text{V}_{\text{GS}}=\pm 20\text{V}, \text{V}_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	nA

### On Characteristics

$\text{R}_{\text{DS(ON)}}$	Static Drain-source On-Resistance	$\text{V}_{\text{GS}}=-10\text{V}, \text{I}_D=-8\text{A}$	---	14.5	18	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=-4.5\text{V}, \text{I}_D=-6\text{A}$	---	23	30	$\text{m}\Omega$
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	$\text{V}_{\text{GS}}=\text{V}_{\text{DS}}, \text{I}_D=250\mu\text{A}$	-1.2	-1.6	-2.5	V
			---	4	---	$\text{mV}/^\circ\text{C}$
$\text{g}_{\text{fs}}$	Forward Transconductance	$\text{V}_{\text{DS}}=-10\text{V}, \text{I}_D=-8\text{A}$	---	6.8	---	S

### Dynamic and Switching Characteristics

$\text{Q}_g$	Total Gate Charge <sup>2,3</sup>	$\text{V}_{\text{DS}}=-15\text{V}, \text{V}_{\text{GS}}=-4.5\text{V}, \text{I}_D=-5\text{A}$	---	11	17	nC
$\text{Q}_{\text{gs}}$	Gate-Source Charge <sup>2,3</sup>		---	3.4	6	
$\text{Q}_{\text{gd}}$	Gate-Drain Charge <sup>2,3</sup>		---	4.2	8	
$\text{T}_{\text{d(on)}}$	Turn-On Delay Time <sup>2,3</sup>	$\text{V}_{\text{DD}}=-15\text{V}, \text{V}_{\text{GS}}=-10\text{V}, \text{R}_G=6\Omega, \text{I}_D=-1\text{A}$	---	5.8	11	ns
$\text{T}_r$	Rise Time <sup>2,3</sup>		---	18.8	36	
$\text{T}_{\text{d(off)}}$	Turn-On Delay Time <sup>2,3</sup>		---	46.9	90	
$\text{T}_f$	Fall Time <sup>2,3</sup>		---	12.3	23	
$\text{C}_{\text{iss}}$	Input Capacitance	$\text{V}_{\text{DS}}=-15\text{V}, \text{V}_{\text{GS}}=0\text{V}, f=1\text{MHz}$	---	1250	2500	pF
$\text{C}_{\text{oss}}$	Output Capacitance		---	160	320	
$\text{C}_{\text{rss}}$	Reverse Transfer Capacitance		---	90	180	

### Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$\text{I}_s$	Continuous Source Current	$\text{V}_G=\text{V}_D=0\text{V}$ , Force Current	---	---	-30	A
$\text{I}_{\text{SM}}$	Pulsed Source Current		---	---	-60	A
$\text{V}_{\text{SD}}$	Diode Forward Voltage	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_s=-1\text{A}, T_J=25^\circ\text{C}$		---	---	-1 V

Note :

- Repetitive Rating : Pulsed width limited by maximum junction temperature.
- The data tested by pulsed , pulse width  $\leq 300\text{us}$  , duty cycle  $\leq 2\%$ .
- Essentially independent of operating temperature.

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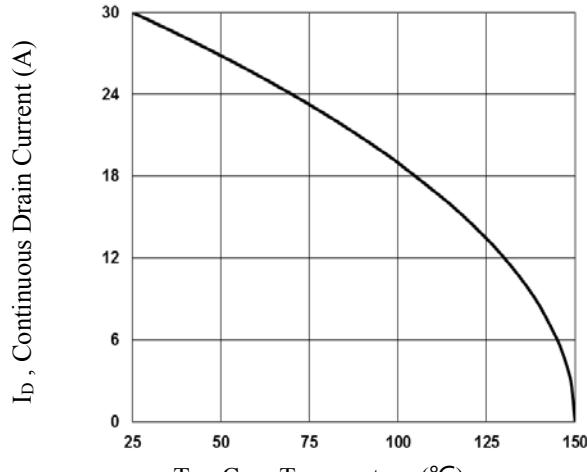


Fig.1      Continuous Drain Current vs. T<sub>C</sub>

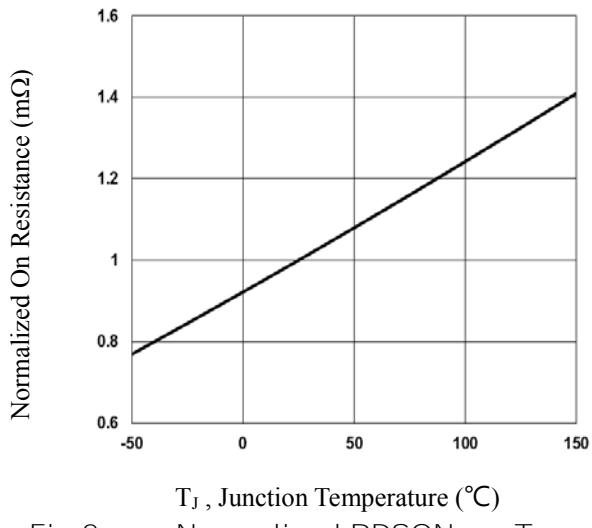


Fig.2      Normalized RDS(on) vs. T<sub>J</sub>

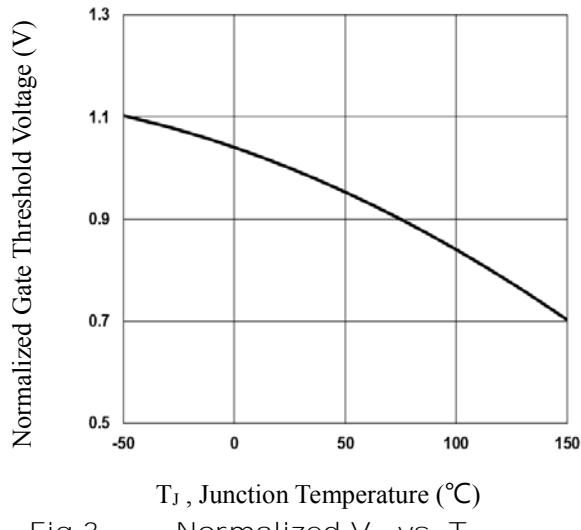


Fig.3      Normalized V<sub>th</sub> vs. T<sub>J</sub>

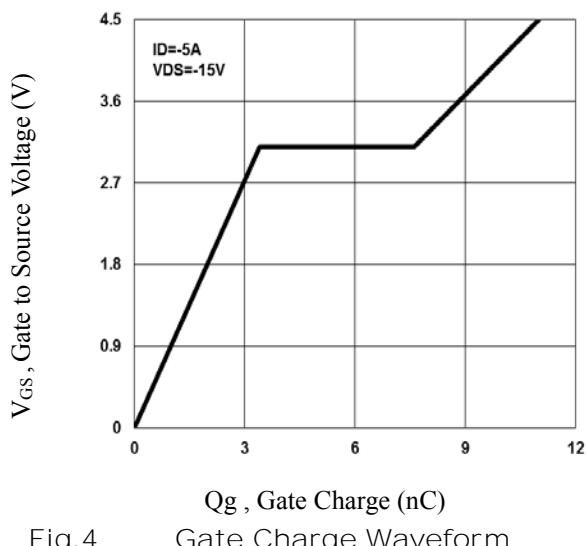


Fig.4      Gate Charge Waveform

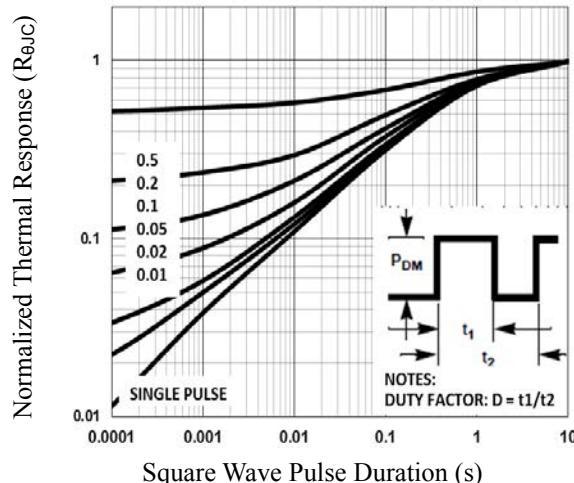


Fig.5      Normalized Transient Impedance

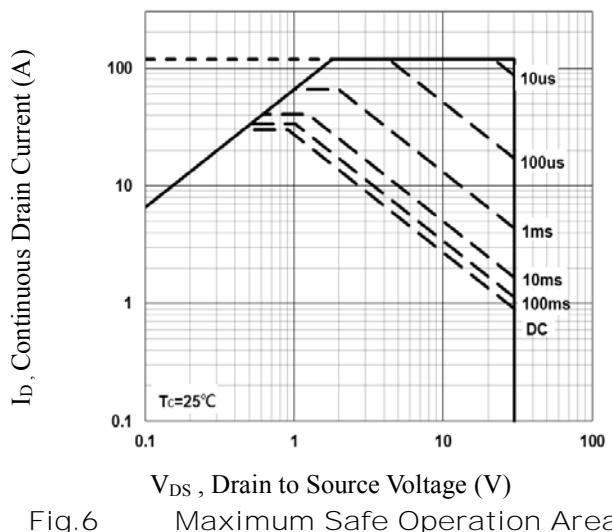


Fig.6      Maximum Safe Operation Area

# DEVICE CHARACTERISTICS

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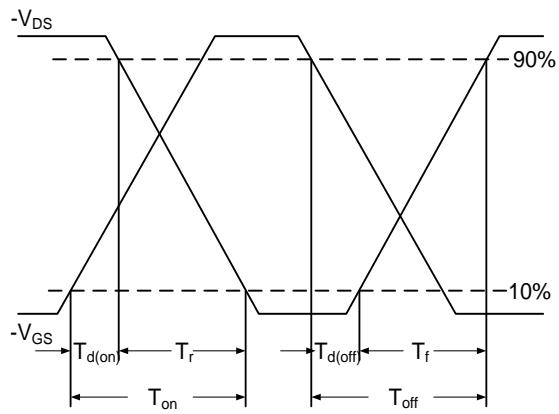


Fig.7 Switching Time Waveform

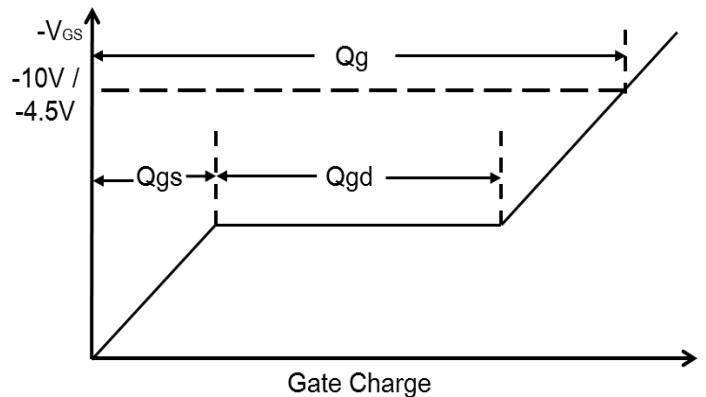
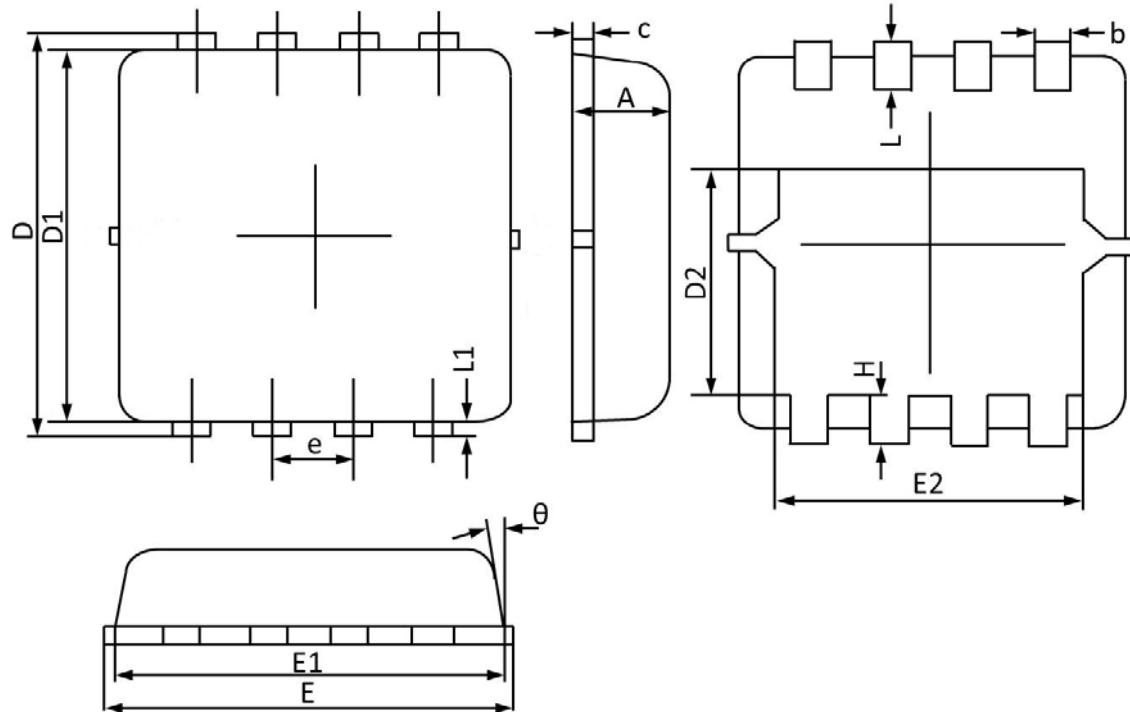


Fig.8 Gate Charge Waveform

# PACKAGE OUTLINE & DIMENSIONS

YS3907ZBB

## PPAK3x3 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.900	0.028	0.035
b	0.240	0.350	0.009	0.014
c	0.100	0.250	0.004	0.010
D	3.050	3.450	0.120	0.136
D1	2.900	3.200	0.114	0.126
D2	1.350	1.850	0.053	0.073
E	3.000	3.400	0.118	0.134
E1	2.900	3.250	0.114	0.128
E2	2.350	2.600	0.093	0.102
e	0.650 BSC		0.026 BSC	
H	0.300	0.500	0.012	0.020
L	0.300	0.500	0.012	0.020
L1	0.070	0.200	0.003	0.008
$\theta$	0°	12°	0°	12°